TRS202E 具有 ±15kV IEC ESD 保护功能的 5V 双路 RS-232 线路驱动器和接收器

1 特性

- 用于 RS-232 总线引脚的 IEC61000-4-2（4 级）ESD 保护：
  - ±8kV 接触放电
  - ±15kV 气隙放电
  - ±15kV 人体放电模型
- 符合或超出 TIA/EIA-232-F 和 ITU v.28 标准的要求
- 由 5V V_{CC} 电源供电
- 速率高达 120kbit/s
- 外部电容器：4 个 0.1μF 或 4 个 1μF
- 闩锁性能超过 100mA，符合 JESD 78 II 级规范

2 应用

- 电池供电型系统
- 笔记本电脑
- 便携式计算机
- 机顶盒
- 手持设备

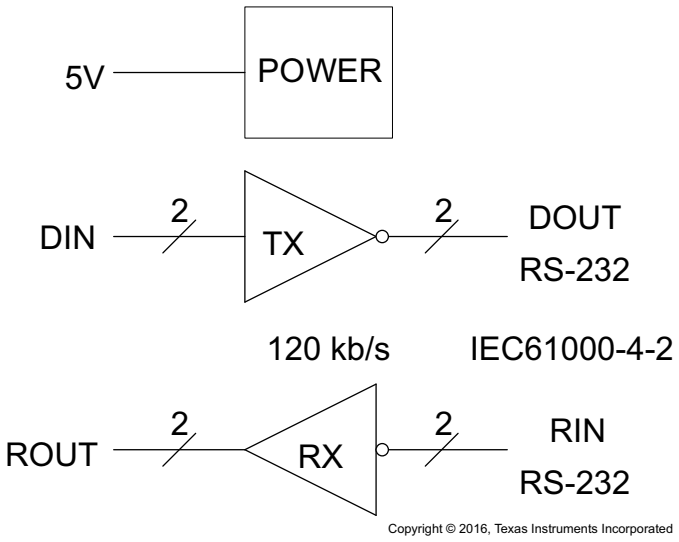
3 说明

TRS202E 由两个线路驱动器、两个线路接收器和一个双路电荷泵电路组成。TRS202E 具有 IEC61000-4-2（4 级）ESD 引脚对引脚（串行端口连接引脚，包括 GND）保护。该器件符合 TIA/EIA-232-F 的要求并在异步通信控制器与串行端口连接器之间提供电气接口。电荷泵和四个小型外部电容器支持由单个 5V 电源供电。该器件以高达 120kbit/s 的数据信号传输速率和最高 30V/μs 的
驱动器输出压摆率运行。

封装信息

器件型号	封装(1)	封装尺寸(2)
TRS202E	SOIC (D) (16)	9.9mm x 6mm
	SOIC (DW) (16)	10.4mm x 10.3mm
	PDIP (N) (16)	19.3mm x 9.4mm
	TSSOP (PW) (16)	5mm x 6.4mm

(1) 如需更多信息，请参阅节 10。
(2) 封装尺寸（长 × 宽）为标称值，并包括引脚（如适用）。



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逻辑图（正逻辑）

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4 Pin Configuration and Functions

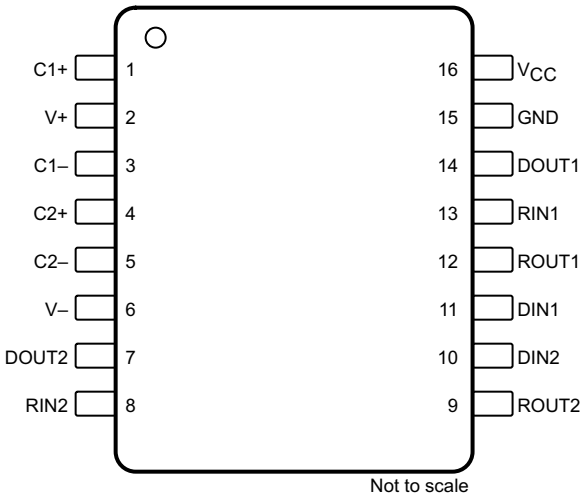


图 4-1. D, DW, N or PW Package, 16-Pin SOIC or TSSOP (Top View)

表 4-1. Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	C1+	—	Positive lead of C1 capacitor
2	V+	O	Positive charge pump output for storage capacitor only
3	C1 –	—	Negative lead of C1 capacitor
4	C2+	—	Positive lead of C2 capacitor
5	C2 –	—	Negative lead of C2 capacitor
6	V –	O	Negative charge pump output for storage capacitor only
7	DOUT2	O	RS-232 line data output (to remote RS-232 system)
8	RIN2	I	RS-232 line data input (from remote RS-232 system)
9	ROUT2	O	Logic data output (to UART)
10	DIN2	I	Logic data input (from UART)
11	DIN1	I	Logic data input (from UART)
12	ROUT1	O	Logic data output (to UART)
13	RIN1	I	RS-232 line data input (from remote RS-232 system)
14	DOUT1	O	RS-232 line data output (to remote RS-232 system)
15	GND	—	Ground
16	V_{CC}	—	Supply voltage, connect to external 5-V power supply

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5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

		MIN	MAX	UNIT
Supply voltage, V_{CC} (2)		–0.3	6	V
Positive charge pump voltage, V+(2)		V_{CC} – 0.3	14	V
Negative charge pump voltage, V–		–14	0.3	V
Input voltage, V_I	Drivers	–0.3	V+ + 0.3	V
	Receivers		±30	
Output voltage, V_O	Drivers	V– – 0.3	V+ + 0.3	V
	Receivers	–0.3	V_{CC} + 0.3	
Short-circuit duration, D_{OUT}		Continuous		
Operating virtual junction temperature, T_J			150	°C
Storage temperature, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to network GND.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	Pins 7, 8, 13, 14, 15	±15000	V
		All other pins	±2000	
	Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	All pins	±1500	
	IEC 61000-4-2 contact discharge	Pins 7, 8, 13, 14, 15	±8000	
	IEC 61000-4-2 air-gap discharge	Pins 7, 8, 13, 14, 15	±15000	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

see 图 7-1 (1)

			MIN	NOM	MAX	UNIT
	Supply voltage		4.5	5	5.5	V
V_{IH}	Driver high-level input voltage (D_{IN})		2			V
V_{IL}	Driver low-level input voltage (D_{IN})				0.8	V
V_I	Driver input voltage (D_{IN})		0		5.5	V
	Receiver input voltage		–30		30	
T_A	Operating free-air temperature	TRS202EC	0		70	°C
		TRS202EI	–40		85	

(1) Test conditions are C1 to C4 = 0.1µF at V_{CC} = 5V ±0.5V.

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5.4 Thermal Information

THERMAL METRIC(1)		D (SOIC)	DW (SOIC)	N (PDIP)	PW (TSSOP)	UNIT
		16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	84.6	77.1	44.1	107.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	43.5	39.9	30.8	38.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.2	41.8	24.2	53.7	°C/W
ψ_{JT}	Junction-to-top characterization parameter	10.4	12.9	15.2	3.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	42.8	41.3	24	53.1	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

5.5 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted; see 图 7-1)(1)

PARAMETER		TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
I_{CC}	Supply current	No load, V_{CC} = 5V		8	15	mA

(1) Test conditions are C1 to C4 = 0.1μF at V_{CC} = 5V + 0.5V.
(2) All typical values are at V_{CC} = 5V and T_A = 25°C.

5.6 Electrical Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 图 7-1)(1)

PARAMETER		TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
V_{OH}	High-level output voltage	D_{OUT} at R_L = 3kΩ to GND, D_{IN} = GND	5	9		V
V_{OL}	Low-level output voltage	D_{OUT} at R_L = 3kΩ to GND, D_{IN} = V_{CC}	–5	–9		V
I_{IH}	High-level input current	V_I = V_{CC}		15	200	μA
I_{IL}	Low-level input current	V_I at 0V		–15	–200	μA
I_{OS} (3)	Short-circuit output current	V_{CC} = 5.5V and V_O = 0V		±10	±60	mA
r_o	Output resistance	V_{CC}, V+, V– = 0V, and V_O = ±2V	300			Ω

(1) Test conditions are C1 to C4 = 0.1μF at V_{CC} = 5V + 0.5V.
(2) All typical values are at V_{CC} = 5V and T_A = 25°C.
(3) Short-circuit durations must be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output must be shorted at a time.

5.7 Electrical Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted; see 图 7-1)(1)

PARAMETER		TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –1mA	3.5	V_{CC} – 0.4		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 5V and T_A = 25°C		1.7	2.4	V
V_{IT-}	Negative-going input threshold voltage	V_{CC} = 5V and T_A = 25°C	0.8	1.2		V
V_{hys}	Input hysteresis (V_{IT+} – V_{IT-})		0.2	0.5	1	V
r_i	Input resistance	V_I = ±3V to ±25V	3	5	7	kΩ

(1) Test conditions are C1 to C4 = 0.1μF at V_{CC} = 5V + 0.5V.
(2) All typical values are at V_{CC} = 5V and T_A = 25°C.

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5.8 Switching Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted; see 图 7-1)(1)

PARAMETER		TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
	Maximum data rate	C_L = 50 to 1000pF, one D_{OUT} switching, and R_L = 3kΩ to 7kΩ (see 图 6-1)	120			kbit/s
$t_{PLH(D)}$	Propagation delay time, low- to high-level output	C_L = 2500pF, all drivers loaded, and R_L = 3kΩ (see 图 6-1)		2		µs
$t_{PHL(D)}$	Propagation delay time, high- to low-level output	C_L = 2500pF, all drivers loaded, and R_L = 3kΩ (see 图 6-1)		2		µs
$t_{sk(p)}$	Pulse skew(3)	C_L = 150 to 2500pF and R_L = 3kΩ to 7kΩ (see 图 6-2)		300		ns
SR(tr)	Slew rate, transition region	C_L = 50 to 1000pF, V_{CC} = 5V, and R_L = 3kΩ to 7kΩ (see 图 6-1)	3	6	30	V/µs

(1) Test conditions are C1 to C4 = 0.1µF at V_{CC} = 5V + 0.5V.
(2) All typical values are at V_{CC} = 5V and T_A = 25°C.
(3) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

5.9 Switching Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted; see 图 6-3)(1)

PARAMETER		TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
$t_{PLH(R)}$	Propagation delay time, low- to high-level output	C_L = 150pF		0.5	10	µs
$t_{PHL(R)}$	Propagation delay time, high- to low-level output	C_L = 150pF		0.5	10	µs
$t_{sk(p)}$	Pulse skew(3)			300		ns

(1) Test conditions are C1 to C4 = 0.1µF at V_{CC} = 5V + 0.5V.
(2) All typical values are at V_{CC} = 5V and T_A = 25°C.
(3) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

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5.10 Typical Characteristics

T_A = 25°C (unless otherwise noted)

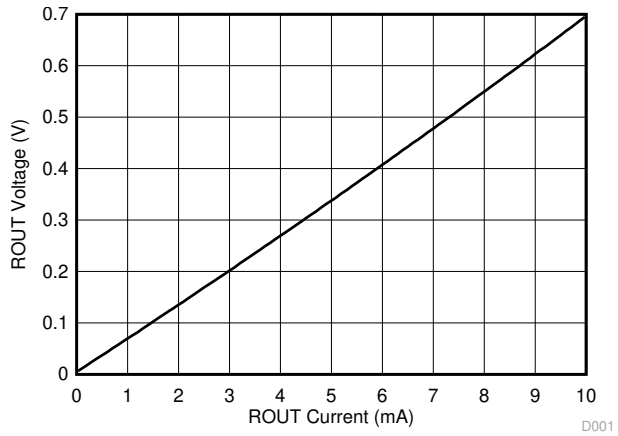


图 5-1. Receiver V_{OL} vs Output Current

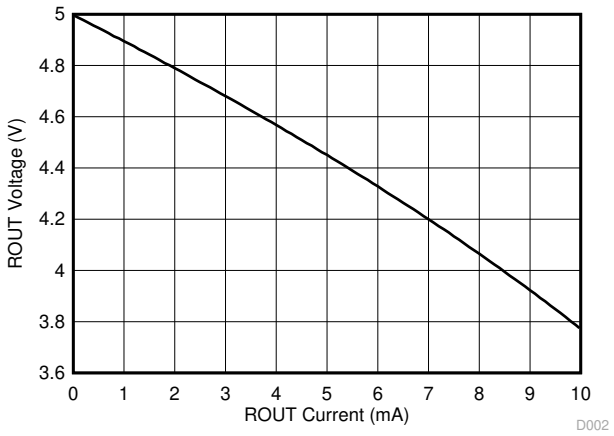


图 5-2. Receiver V_{OH} vs Output Current

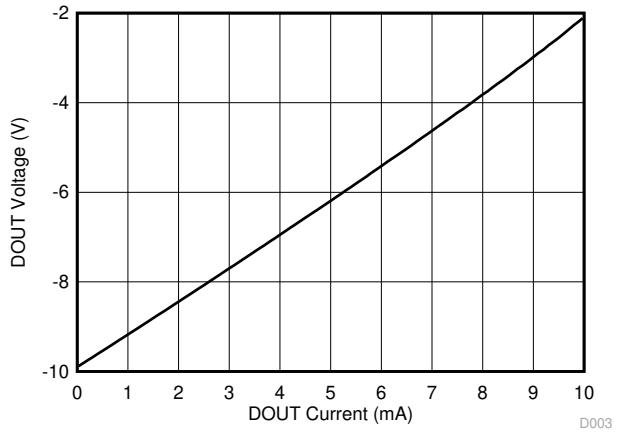


图 5-3. Driver V_{OL} vs Output Current

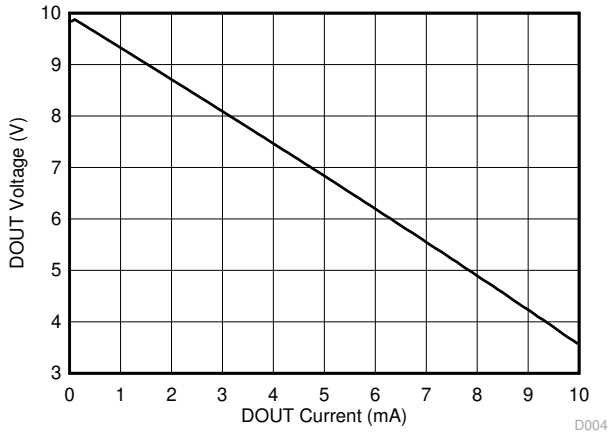


图 5-4. Driver V_{OH} vs Output Current

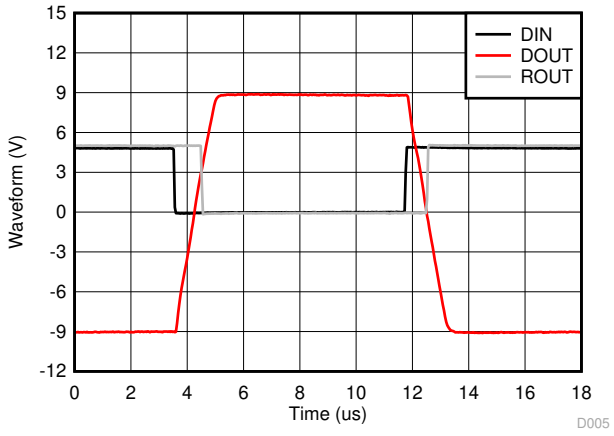
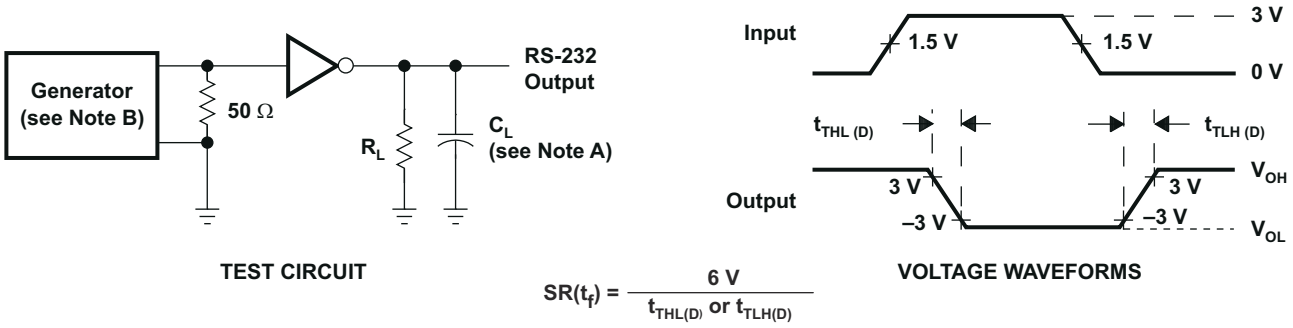


图 5-5. Driver and Receiver Loopback Waveforms

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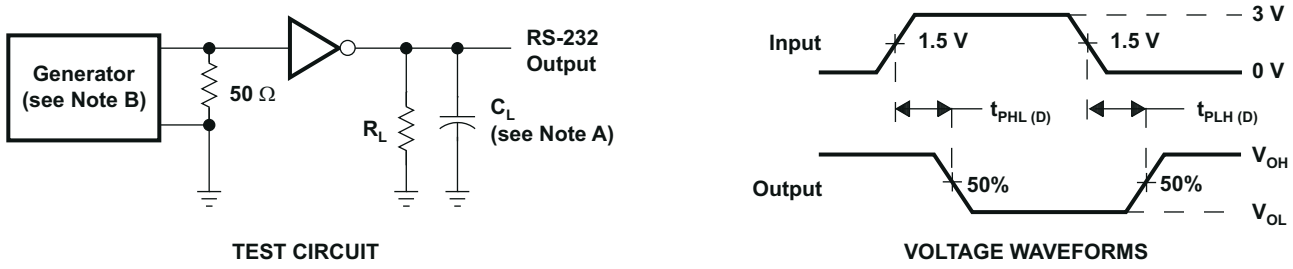
Parameter Measurement Information



$$SR(t_f) = \frac{6\ V}{t_{THL(D)} \text{ or } t_{TLH(D)}}$$

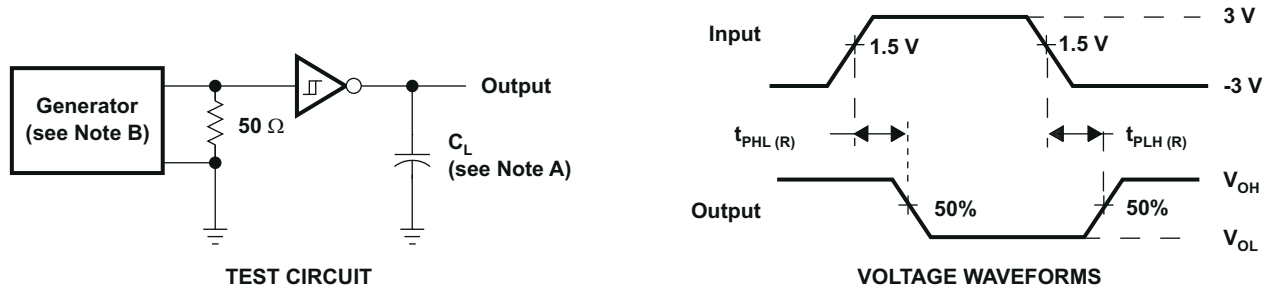
NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 120 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

图 6-1. Driver Slew Rate



NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 120 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

图 6-2. Driver Pulse Skew



NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

图 6-3. Receiver Propagation Delay Times

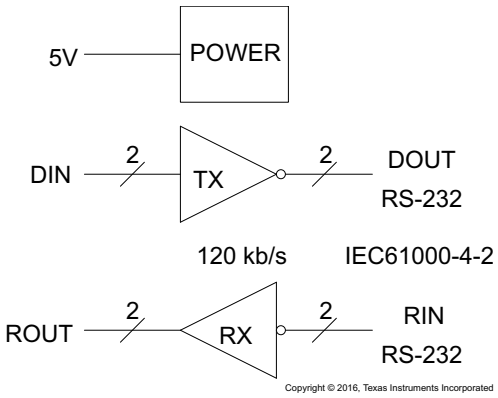
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6 Detailed Description

6.1 Overview

The TRS202E device is a dual driver and receiver that includes a capacitive voltage generator using four capacitors to supply TIA/EIA-232-F voltage levels from a single 5V supply. All RS-232 pins have 15kV HBM and IEC61000-4-2 Air-Gap discharge protection. RS-232 pins also have 8-kV IEC61000-4-2 contact discharge protection. Each receiver converts TIA/EIA-232-F inputs to 5V TTL/CMOS levels. These receivers have shorted and open fail safe. The receiver can accept up to ±30V inputs and decode inputs as low as ±3V. Each driver converts TTL/CMOS input levels into TIA/EIA-232-F levels. Outputs are protected against shorts to ground.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Power

The power block increases and inverts the 5V supply for the RS-232 driver using a charge pump that requires four 0.1µF or 1µF external capacitors.

6.3.2 RS-232 Driver

Two drivers interface standard logic levels to RS-232 levels. The driver inputs do not have internal pullup resistors. Do not float the driver inputs.

6.3.3 RS-232 Receiver

Two Schmitt trigger receivers interface RS-232 levels to standard logic levels. Each receiver has an internal 5-kΩ load to ground. An open input results in a high output on R_{OUT}.

6.4 Device Functional Modes

6.4.1 V_{CC} Powered by 5V

The device is in normal operation when powered by 5V.

6.4.2 V_{CC} Unpowered

When TRS202E is unpowered, it can be safely connected to an active remote RS-232 device.

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6.4.3 Truth Tables

表 6-1 and 表 6-2 list the function for each driver and receiver (respectively).

表 6-1. Function Table for Each Driver

INPUT DIN(1)	OUTPUT DOUT
L	H
H	L

(1) H = high level, L = low level

表 6-2. Function Table for Each Receiver

INPUT RIN(1)	OUTPUT ROUT
L	H
H	L
Open	H

(1) H = high level, L = low level,
Open = input disconnected or connected driver off

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7 Application and Implementation

备注

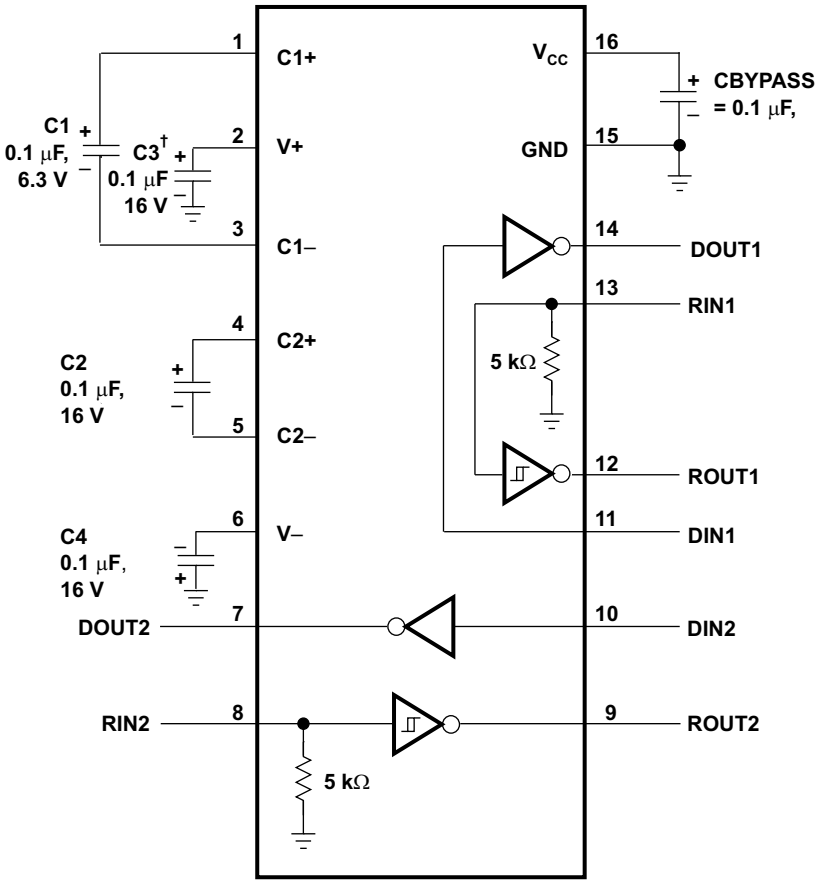
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7.1 Application Information

For proper operation, add capacitors as shown in 图 7-1. Pins 9 through 12 connect to UART or general purpose logic lines. RS-232 lines on pins 7, 8, 13, and 14 connect to a connector or cable.

7.2 Typical Application

Two driver and two receiver channels are supported for full duplex transmission with hardware flow control. The two 5kΩ-resistors are internal to the TRS202E.



† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

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图 7-1. Typical Operating Circuit and Capacitor Values

7.2.1 Design Requirements

- V_{CC} minimum is 4.5V and maximum is 5.5V.
- Maximum recommended bit rate is 120kbps.

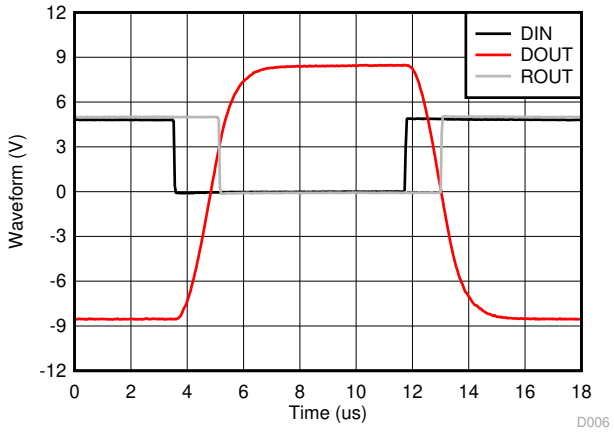
7.2.2 Detailed Design Procedure

7.2.2.1 Capacitor Selection

The capacitor type used for C1 through C4 is not critical for proper operation. The TRS202E requires 0.1µF capacitors. 1-µF capacitors are also acceptable. TI recommends ceramic dielectrics. When using the minimum recommended capacitor values, ensure the capacitance value does not degrade excessively as the operating temperature varies. If in doubt, use capacitors with a larger (for example, 2×) nominal value. The capacitors' effective series resistance (ESR), which usually rises at low temperatures, influences the amount of ripple on V+ and V – .

Bypass V_{CC} to ground with at least 0.1µF. In applications sensitive to power-supply noise generated by the charge pumps, decouple V_{CC} to ground with a capacitor the same size as (or larger than) the charge-pump capacitors (C1 to C4).

7.2.3 Application Curves



120 kbit/s, 1-nF load

图 7-2. Driver and Receiver Loopback Signal

7.3 Power Supply Recommendations

The V_{CC} voltage must be connected to the same power source used for logic device connected to DIN and ROUT pins. V_{CC} must be between 4.5V and 5.5V.

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7.4 Layout

7.4.1 Layout Guidelines

Keep the external capacitor traces short. This is more important on C1 and C2 nodes that have the fastest rise and fall times. Make the impedance from TRS202E ground pin and circuit boards ground plane as low as possible for best ESD performance. Use wide metal and multiple vias on both sides of ground pin.

7.4.2 Layout Example

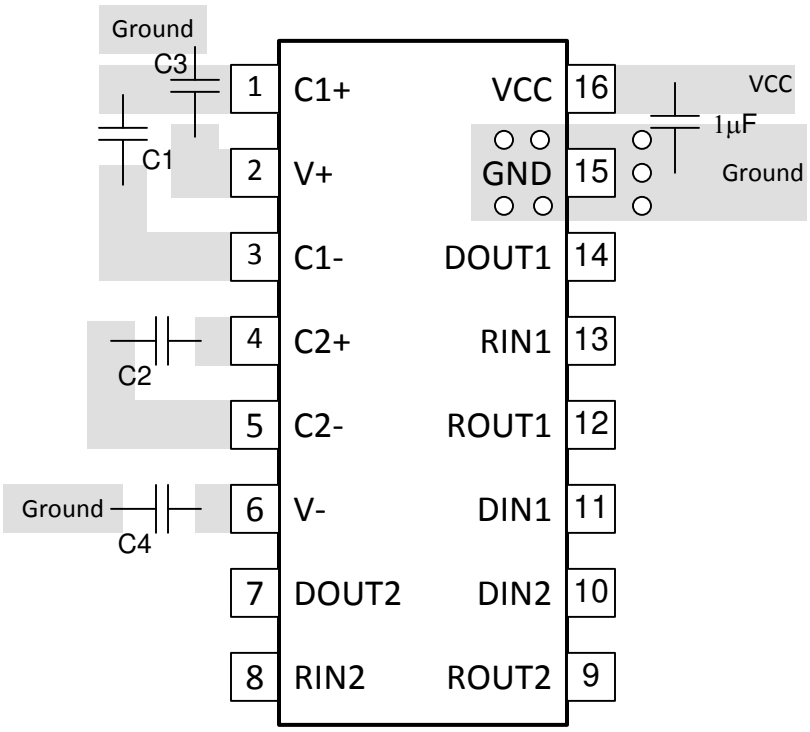


图 7-3. TRS202E Layout

8 Device and Documentation Support

8.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

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TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

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所有商标均为其各自所有者的财产。

8.4 静电放电警告

静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

8.5 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

9 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision E (November 2016) to Revision F (February 2024) — **Page**

- 更改了 *封装信息* 表 1
- Changed the *Thermal Information* table 5

Changes from Revision D (November 2012) to Revision E (November 2016) — **Page**

- 添加了 *ESD 等级* 表、*特性说明* 部分、*器件功能模式*、*应用和实现* 部分、*电源相关建议* 部分、*布局* 部分、*器件和文档支持* 部分以及 *机械、封装和可订购信息* 部分 1
- 删除了 *订购信息* 表，请参阅数据表末尾的 *封装选项附录* 1
- Changed Package thermal impedance, $R_{\theta JA}$, values in Thermal Information table From: 73°C/W To: 76.7°C/W (D), From: 57°C/W To: 77.1°C/W (DW), From: 67°C/W To: 44.1°C/W (N), and From: 108°C/W To: 101.7°C/W (PW) 5

Changes from Revision C (May 2010) to Revision D (November 2012) — **Page**

- Fixed I_{OS} values in *Electrical Characteristics* table, changed – to ± 5

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10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TRS202ECD	Obsolete	Production	SOIC (D) | 16	-	-	Call TI	Call TI	0 to 70	TRS202EC
TRS202ECDR	Obsolete	Production	SOIC (D) | 16	-	-	Call TI	Call TI	0 to 70	TRS202EC
TRS202ECDWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TRS202EC
TRS202ECDWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TRS202EC
TRS202ECN	Active	Production	PDIP (N) | 16	25 | TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TRS202ECN
TRS202ECN.A	Active	Production	PDIP (N) | 16	25 | TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TRS202ECN
TRS202ECPW	Obsolete	Production	TSSOP (PW) | 16	-	-	Call TI	Call TI	0 to 70	RU02EC
TRS202ECPWR	Obsolete	Production	TSSOP (PW) | 16	-	-	Call TI	Call TI	0 to 70	RU02EC
TRS202EID	Obsolete	Production	SOIC (D) | 16	-	-	Call TI	Call TI	-40 to 85	TRS202EI
TRS202EIDR	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS202EI
TRS202EIDR.A	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS202EI
TRS202EIDW	Active	Production	SOIC (DW) | 16	40 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS202EI
TRS202EIDW.A	Active	Production	SOIC (DW) | 16	40 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS202EI
TRS202EIDWR	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS202EI
TRS202EIDWR.A	Active	Production	SOIC (DW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRS202EI
TRS202EIN	Active	Production	PDIP (N) | 16	25 | TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	TRS202EIN
TRS202EIN.A	Active	Production	PDIP (N) | 16	25 | TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	TRS202EIN
TRS202EIPWR	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RU02EI
TRS202EIPWR.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RU02EI
TRS202EIPWRG4	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RU02EI
TRS202EIPWRG4.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	RU02EI

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

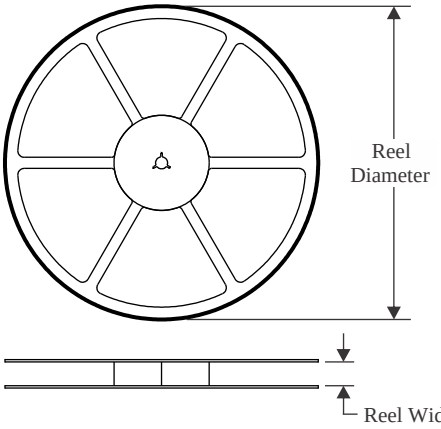
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

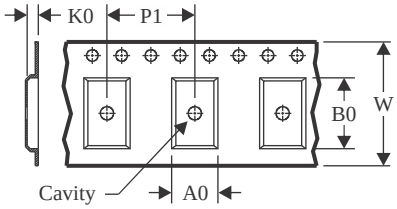
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

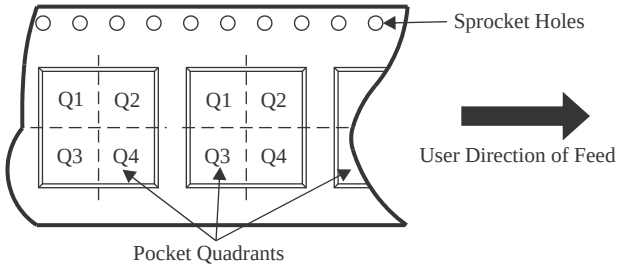


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

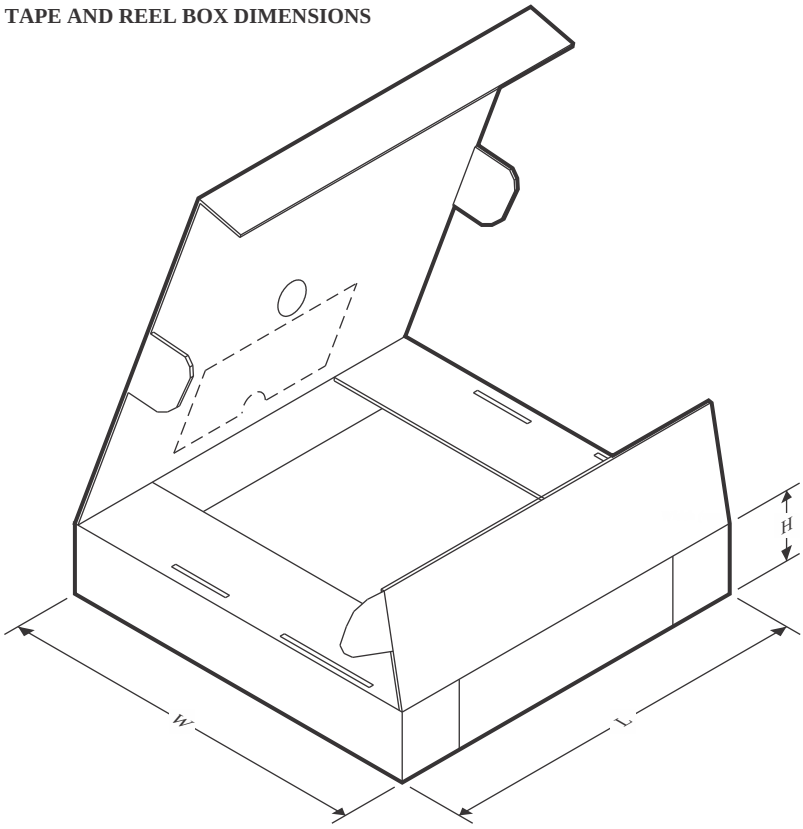
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TRS202ECDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
TRS202EIDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TRS202EIDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
TRS202EIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TRS202EIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TRS202EIPWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

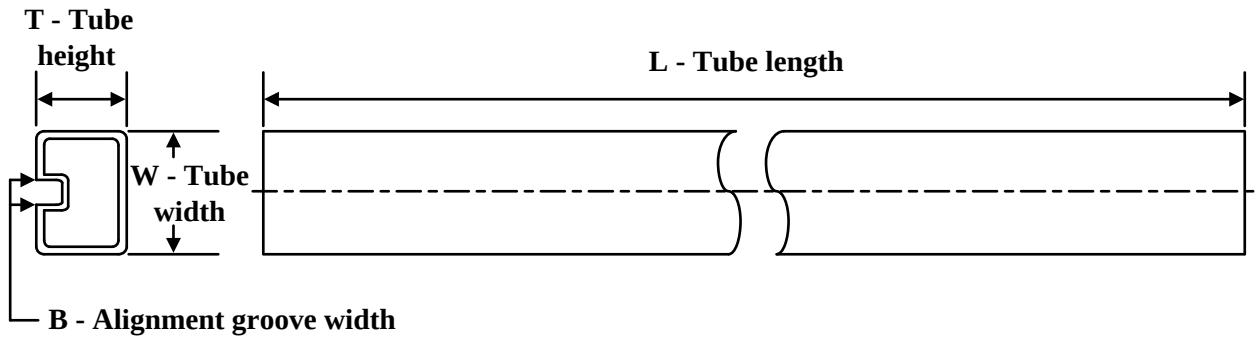
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TRS202ECDWR	SOIC	DW	16	2000	350.0	350.0	43.0
TRS202EIDR	SOIC	D	16	2500	340.5	336.1	32.0
TRS202EIDWR	SOIC	DW	16	2000	350.0	350.0	43.0
TRS202EIPWR	TSSOP	PW	16	2000	367.0	367.0	35.0
TRS202EIPWR	TSSOP	PW	16	2000	353.0	353.0	32.0
TRS202EIPWRG4	TSSOP	PW	16	2000	353.0	353.0	32.0

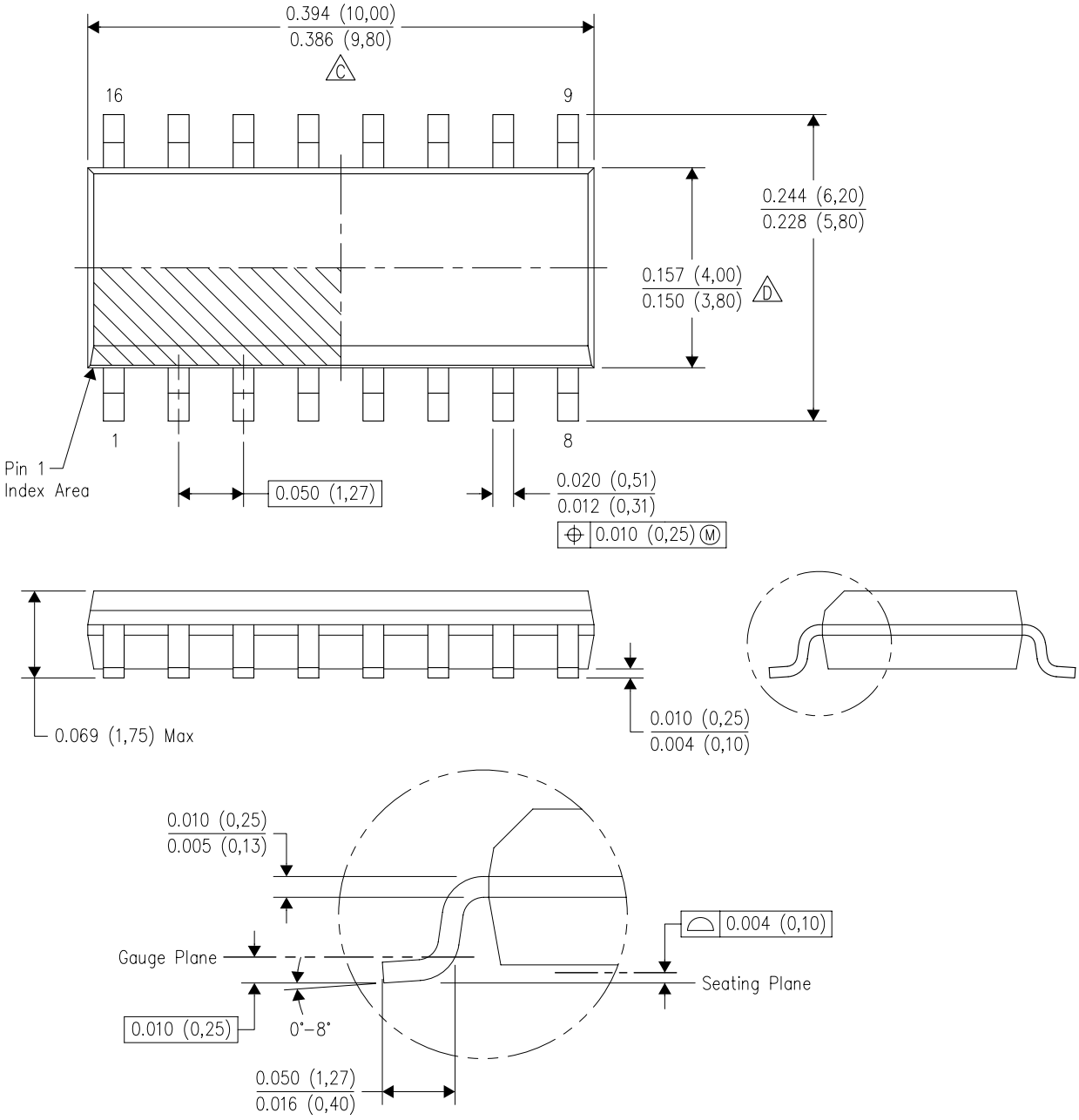
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TRS202ECN	N	PDIP	16	25	506	13.97	11230	4.32
TRS202ECN.A	N	PDIP	16	25	506	13.97	11230	4.32
TRS202EIDW	DW	SOIC	16	40	506.98	12.7	4826	6.6
TRS202EIDW.A	DW	SOIC	16	40	506.98	12.7	4826	6.6
TRS202EIN	N	PDIP	16	25	506	13.97	11230	4.32
TRS202EIN.A	N	PDIP	16	25	506	13.97	11230	4.32

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

GENERIC PACKAGE VIEW

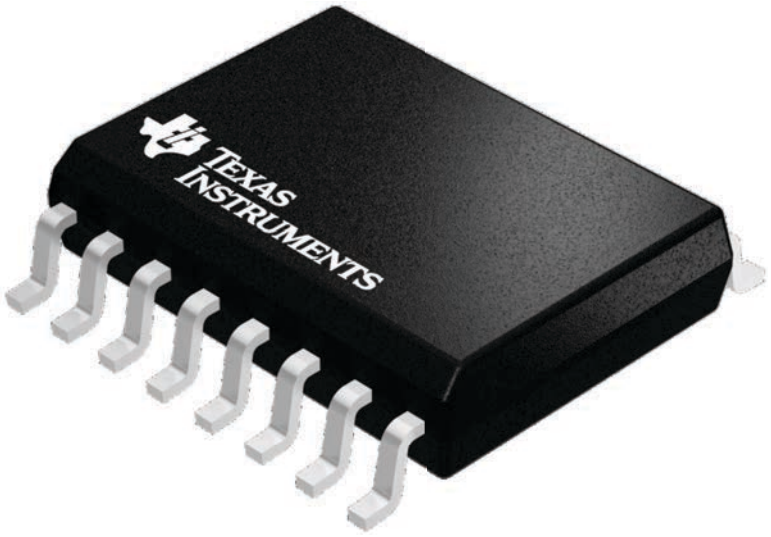
DW 16

SOIC - 2.65 mm max height

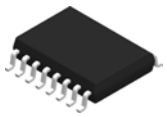
7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4224780/A

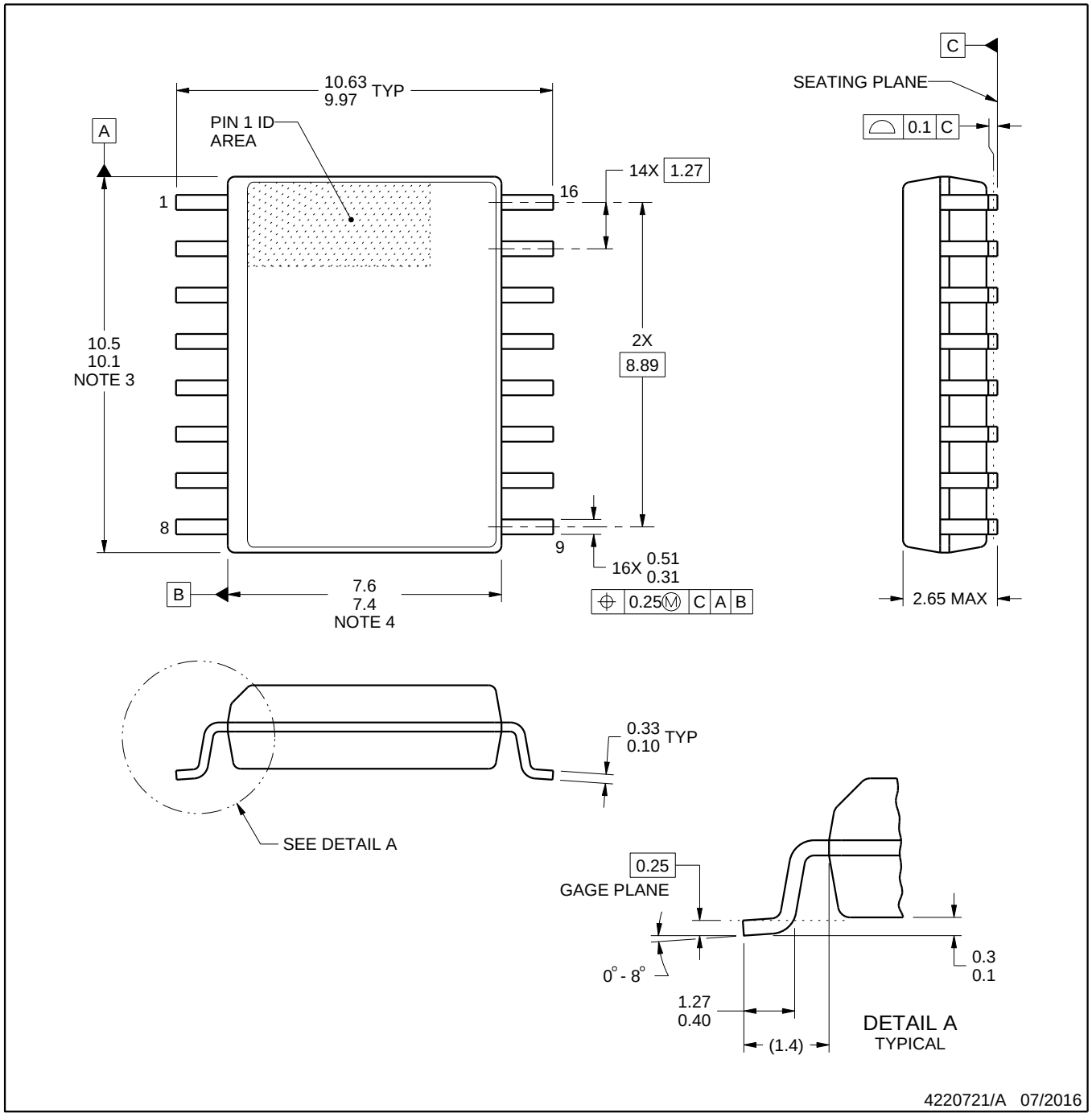


PACKAGE OUTLINE

DW0016A

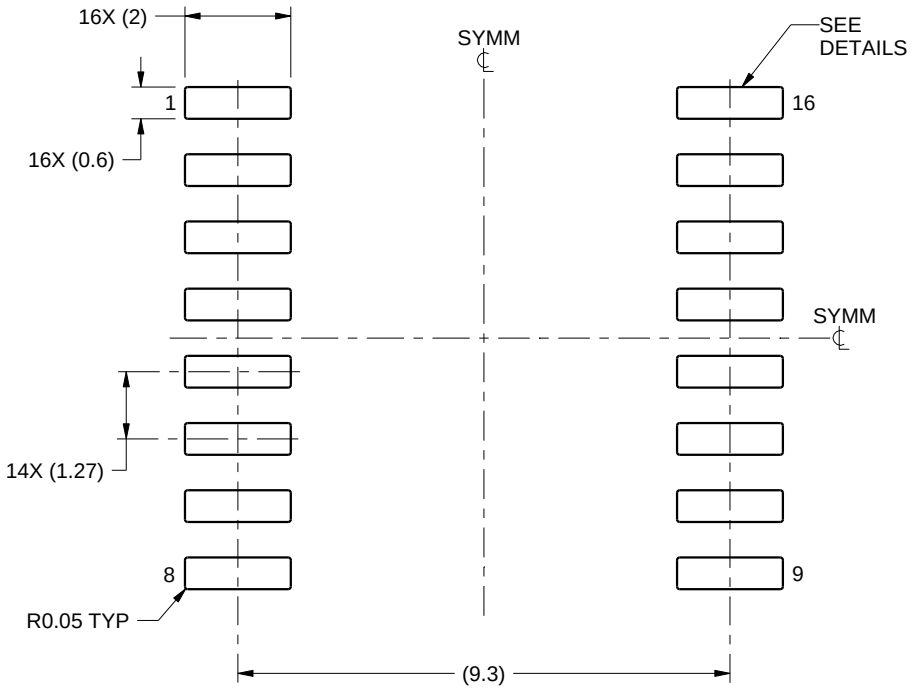
SOIC - 2.65 mm max height

SOIC

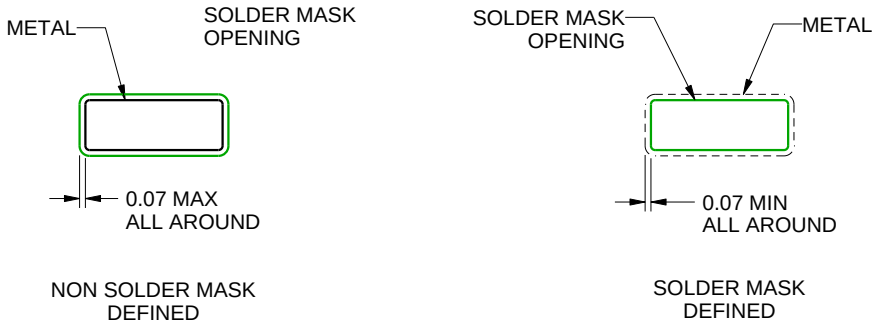


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.



LAND PATTERN EXAMPLE
SCALE:7X

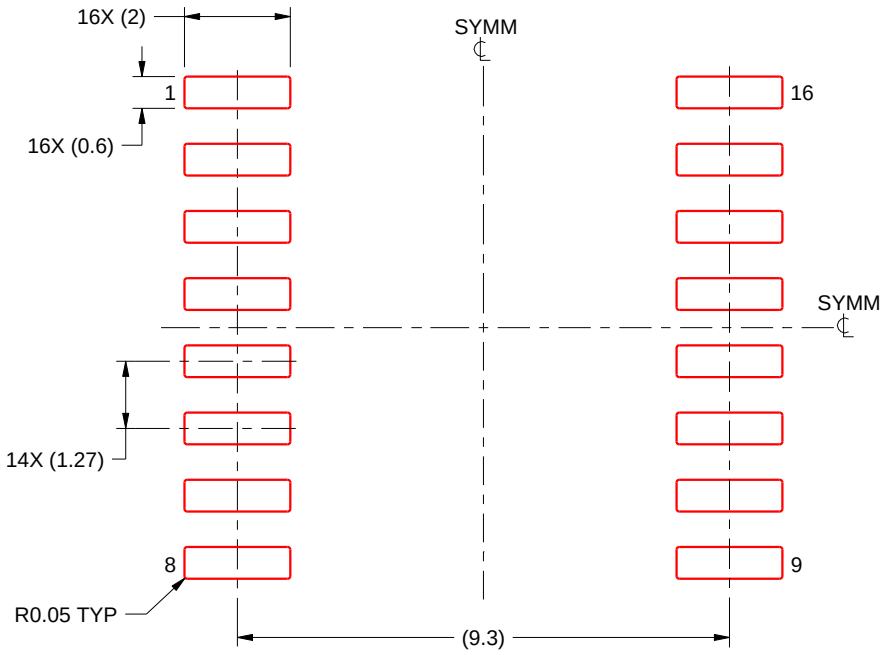


SOLDER MASK DETAILS

4220721/A 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:7X

4220721/A 07/2016

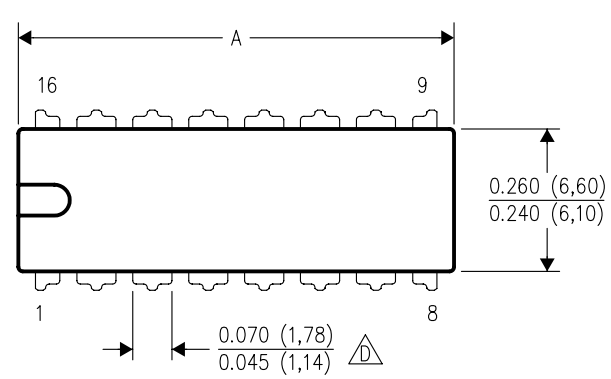
NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

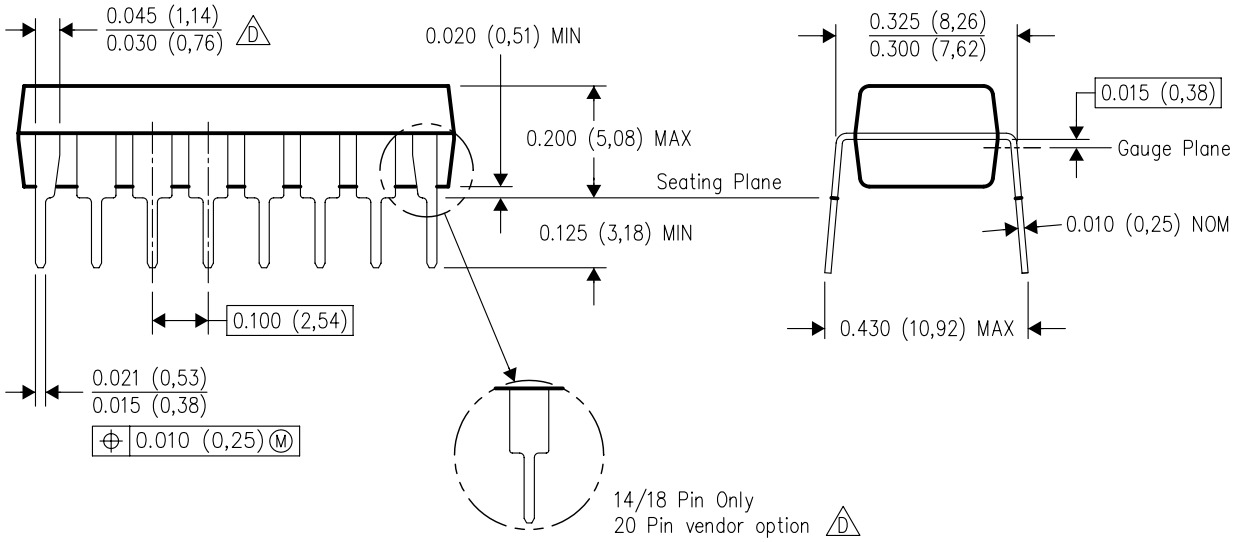
N (R–PDIP–T**)

PLASTIC DUAL–IN–LINE PACKAGE

16 PINS SHOWN



DIM \ PINS **	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS–001 VARIATION (C)	AA	BB	AC	AD



4040049/E 12/2002

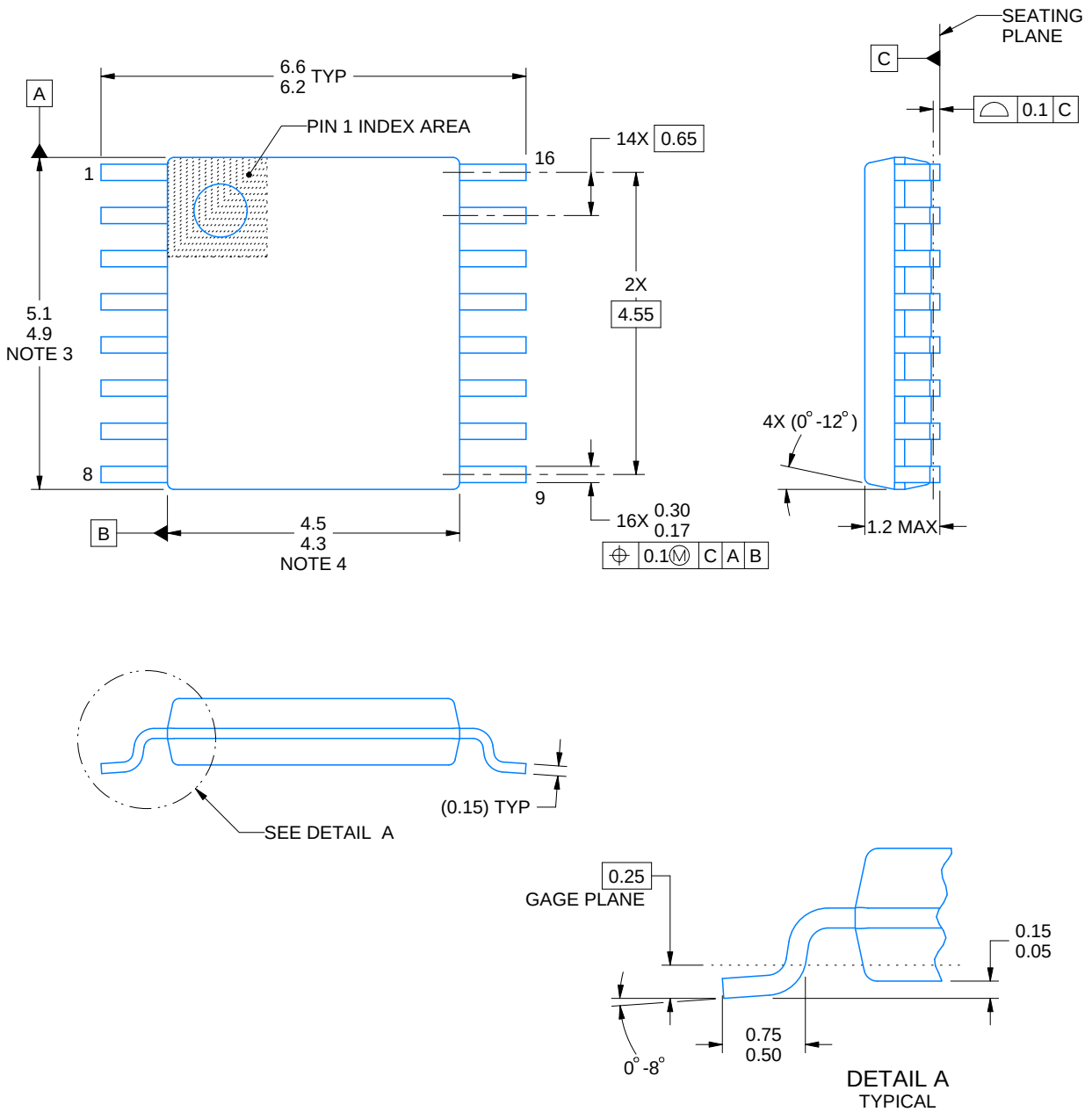
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001, except 18 and 20 pin minimum body length (Dim A).
D. The 20 pin end lead shoulder width is a vendor option, either half or full width.

PACKAGE OUTLINE

PW0016A

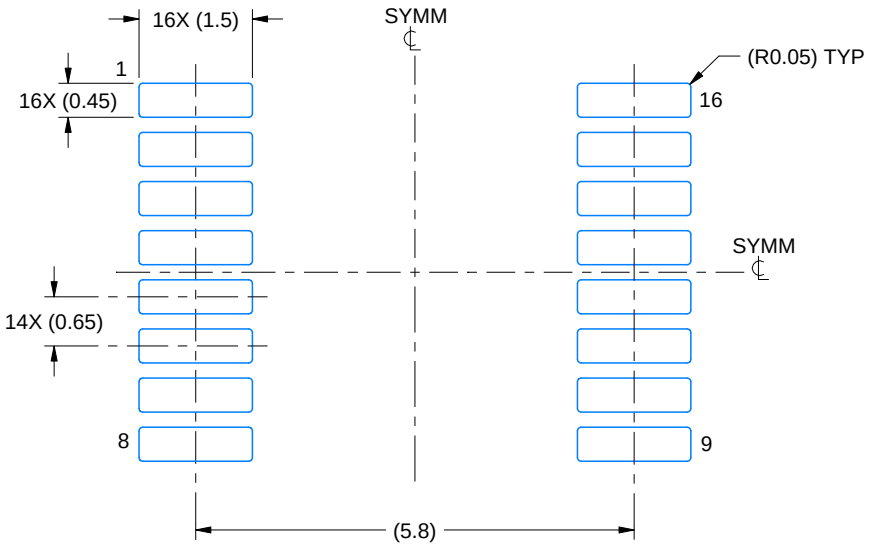
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

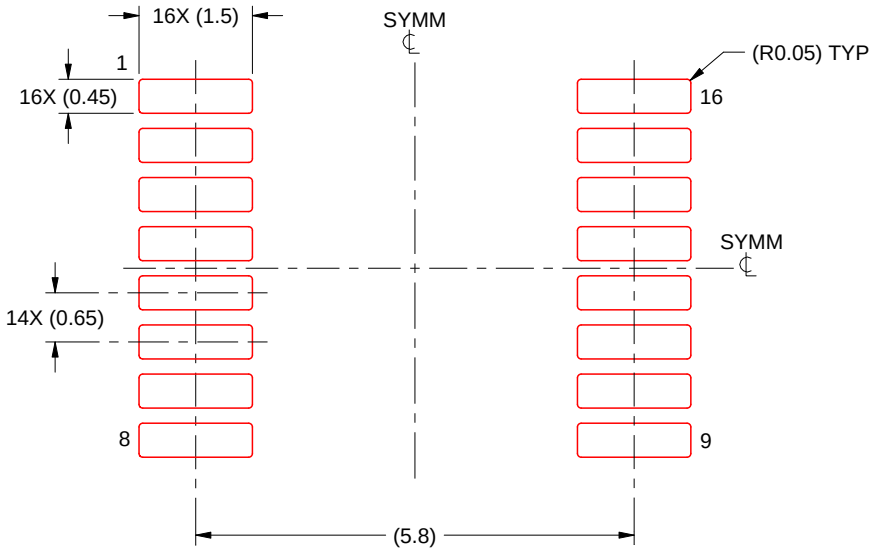


SOLDER MASK DETAILS

4220204/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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最后更新日期：2025 年 10 月